

**METHOD OF ETCHING A SEMICONDUCTOR DEVICE**Abstract

5 A method for etching windows 40 in a semiconductor device 10 having a metal fuse 14  
embedded therein is disclosed. The method is for allowing accurate fuse blowing, in  
particular laser fuse blowing. The method involves the controlled removal of layers  
having different phase diffraction characteristics. After treatment, the remaining area  
between the metal fuse 14 and the etched surface of the semiconductor has substantially  
10 uniform phase diffraction characteristics.

Figure 3